

Spezifikationen	
Teilenummer	JANTXV2N7371
Hersteller	Microsemi
Beschreibung	TRANS PNP DARL 100V 12A TO254
Kategorie	Diskrete Halbleiterprodukte > Transistoren-Bipolar
Teilstatus	2561 pcs Stock
Spannung - Kollektor-Emitter-Durchbruch (max)	100V
VCE Sättigung (Max) @ Ib, Ic	3V @ 120mA, 12A
Transistor-Typ	PNP - Darlington
Supplier Device-Gehäuse	TO-254AA
Serie	Military, MIL-PRF-19500/623
Leistung - max	100W
Verpackung	Bulk
Verpackung / Gehäuse	TO-254-3, TO-254AA (Straight Leads)
Betriebstemperatur	-65°C ~ 200°C (TJ)
Befestigungsart	Through Hole
Frequenz - Übergang	-
DC Stromgewinn (HFE) (Min) @ Ic, VCE	1000 @ 6A, 3V
Strom - Collector Cutoff (Max)	1mA
Strom - Kollektor (Ic) (max)	12A

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JANTXV2N7373
Microsemi Corporation
TRANS NPN 80V 5A TO254


JANTXV2N7334
Microsemi Corporation
MOSFET 4N-CH 100V 1A MO-
036AB




JANTXV2N7370
Microsemi Corporation
TRANS NPN DARL 100V 12A
TO254

 **JANTXV2N7335**
Microsemi Corporation
MOSFET 4P-CH 100V 0.75A MO-036AB

 **JANTXV2N7369**
Microsemi Corporation
TRANS PNP 80V 10A TO254


JANTXV2N7335
Microsemi Corporation
MOSFET 4P-CH 100V 0.75A MO-036AB

Mehr

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